

General Description

These N-channel MOSFET are produced using advanced Magnachip's MOSFET Technology, which provides low on-state resistance, high switching performance and excellent quality.

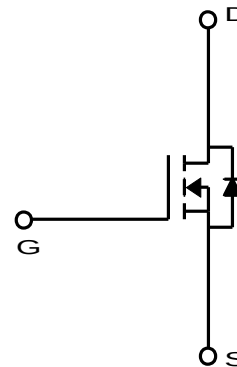
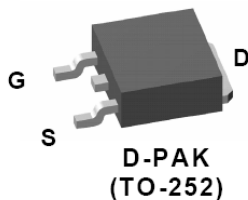
These devices are suitable device for SMPS, high Speed switching and general purpose applications.

Features

- $V_{DS} = 250V$
- $I_D = 10.2A$
- $R_{DS(ON)} \leq 0.28\Omega$ @ $V_{GS} = 10V$

Applications

- Power Supply
- Motor Control
- High Current, High Speed Switching



Absolute Maximum Ratings ($T_a = 25^\circ C$)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	250	V
Gate-Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current	$T_C = 25^\circ C$	I_D	10.2	A
	$T_C = 100^\circ C$		6.4	A
Pulsed Drain Current ⁽¹⁾		I_{DM}	40.8	A
Power Dissipation	$T_C = 25^\circ C$	P_D	69.4	W
	Derivate above $25^\circ C$		0.56	W/ $^\circ C$
Peak Diode Recovery dv/dt ⁽³⁾		dv/dt	4.5	V/ns
Repetitive Avalanche Energy ⁽¹⁾		E_{AR}	6.94	mJ
Avalanche current ⁽¹⁾		I_{AR}	10.2	A
Single Pulse Avalanche Energy ⁽⁴⁾		E_{AS}	550	mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~150	$^\circ C$

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient ⁽¹⁾	$R_{\theta JA}$	110	$^\circ C/W$
Thermal Resistance, Junction-to-Case ⁽¹⁾	$R_{\theta JC}$	1.8	

Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
MDD14N25CRH	-55~150°C	D-pak	Reel & Tape	Halogen Free

Electrical Characteristics (Ta =25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V	250	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.0	-	4.0	
Drain Cut-Off Current	I _{DSS}	V _{DS} = 250V, V _{GS} = 0V	-	-	1	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±30V, V _{DS} = 0V	-	-	100	nA
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 5.1 A	-	0.22	0.28	Ω
Forward Transconductance	g _{fs}	V _{DS} = 30V, I _D = 5.1A	-	8.5	-	S
Dynamic Characteristics						
Total Gate Charge	Q _g	V _{DS} = 200V, I _D = 14.0A, V _{GS} = 10V	-	20.0	-	nC
Gate-Source Charge	Q _{gs}		-	4.5	-	
Gate-Drain Charge	Q _{gd}		-	8.9	-	
Input Capacitance	C _{iss}	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	-	741	-	pF
Reverse Transfer Capacitance	C _{rss}		-	15	-	
Output Capacitance	C _{oss}		-	142	-	
Turn-On Delay Time	t _{d(on)}	V _{GS} = 10V, V _{DS} = 125V, I _D = 14.0A, R _G = 25Ω ⁽³⁾	-	13	-	ns
Rise Time	t _r		-	42	-	
Turn-Off Delay Time	t _{d(off)}		-	44	-	
Fall Time	t _f		-	28	-	
Drain-Source Body Diode Characteristics						
Maximum Continuous Drain to Source Diode Forward Current	I _S		-	-	10.2	A
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 10.2A, V _{GS} = 0V	-	-	1.4	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 14.0A, dI/dt = 100A/μs ⁽³⁾	-	174	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	1.0	-	μC

Note :

1. Pulse width is based on $R_{\theta JC}$ & $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C.
2. Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ C$.
3. $I_{SD} \leq 10.2A$, $di/dt \leq 300A/\mu s$, $V_{DD} \leq BV_{dss}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ C$
4. $L = 8.5mH$, $I_{AS} = 10.2A$, $V_{DD} = 50V$, $R_G = 26\Omega$, Starting $T_J = 25^\circ C$

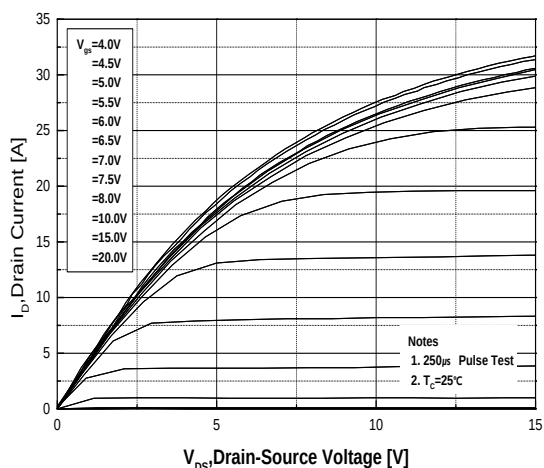


Fig.1 On-Region Characteristics

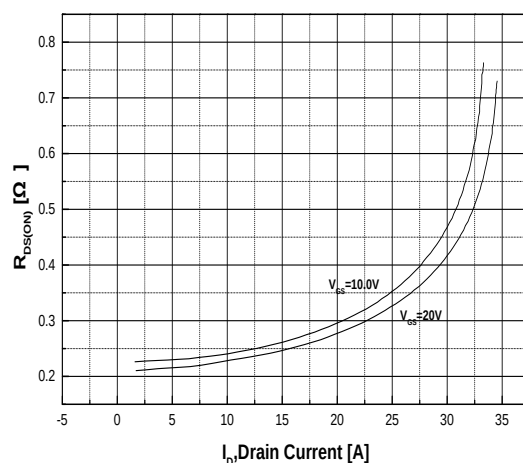


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

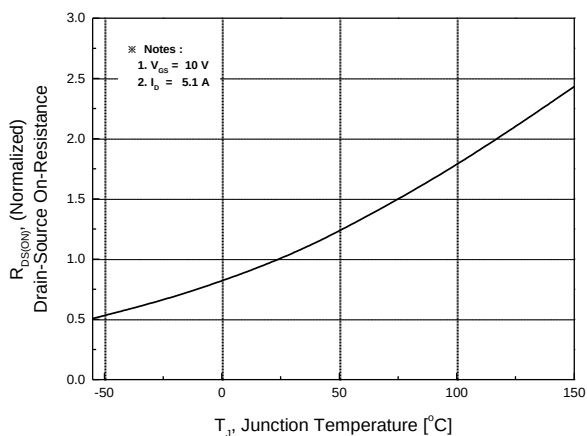


Fig.3 On-Resistance Variation with Temperature

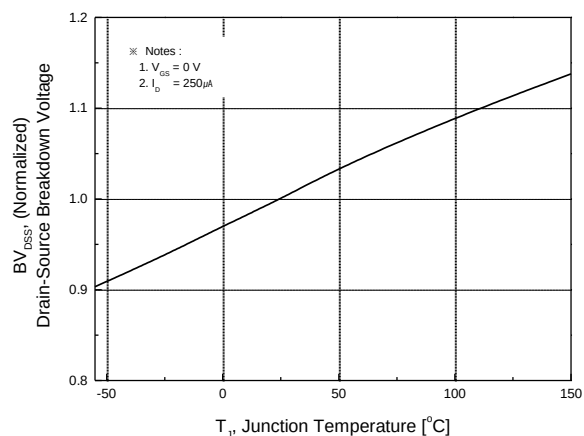


Fig.4 Breakdown Voltage Variation vs. Temperature

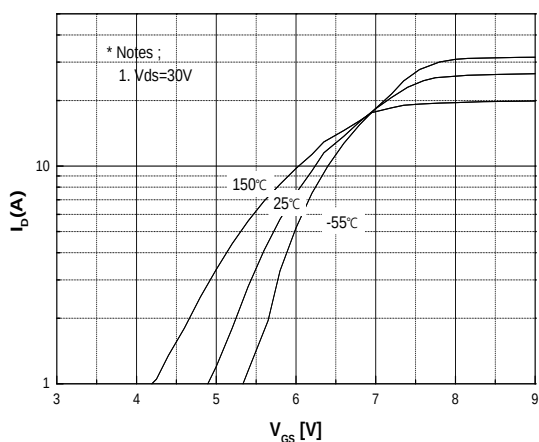


Fig.5 Transfer Characteristics

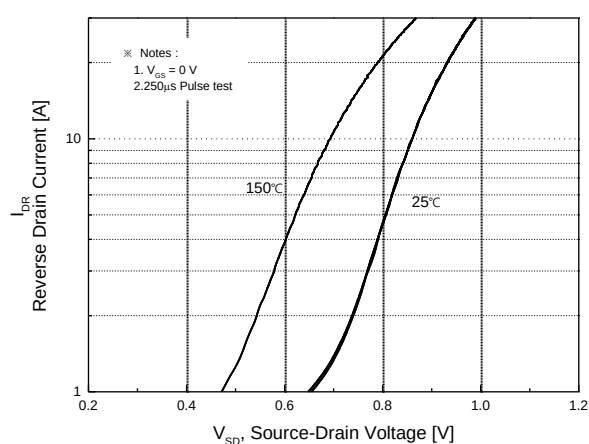


Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature

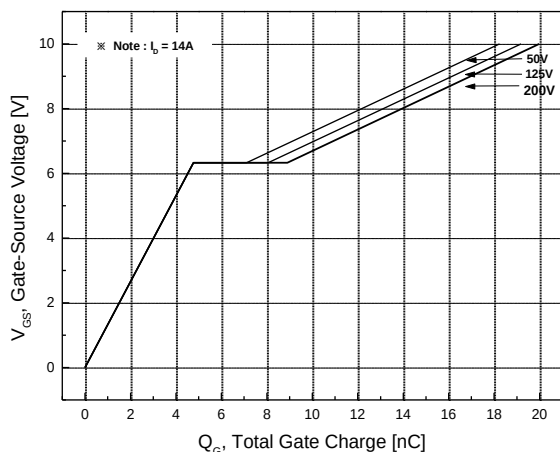


Fig.7 Gate Charge Characteristics

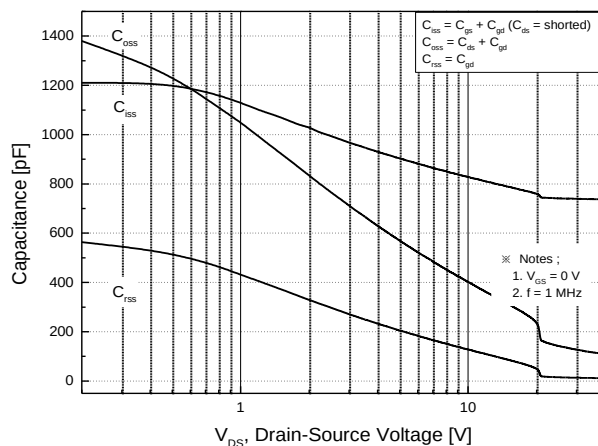


Fig.8 Capacitance Characteristics

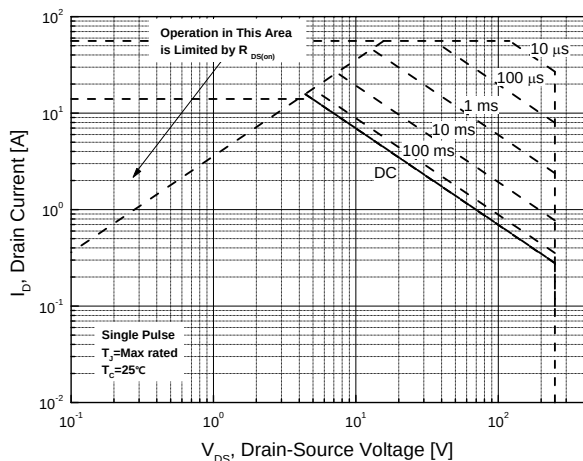


Fig.9 Maximum Safe Operating Area

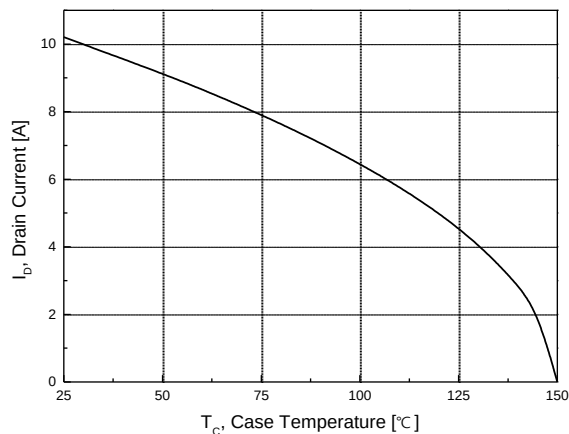


Fig.10 Maximum Drain Current vs. Case Temperature

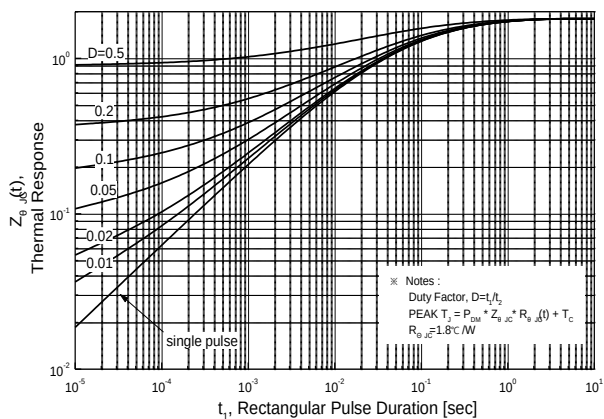


Fig.11 Transient Thermal Response Curve

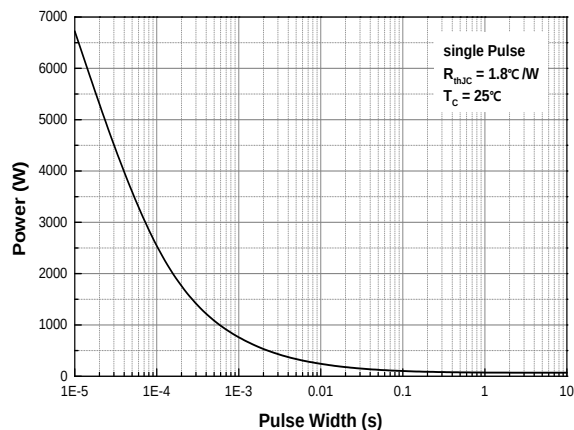
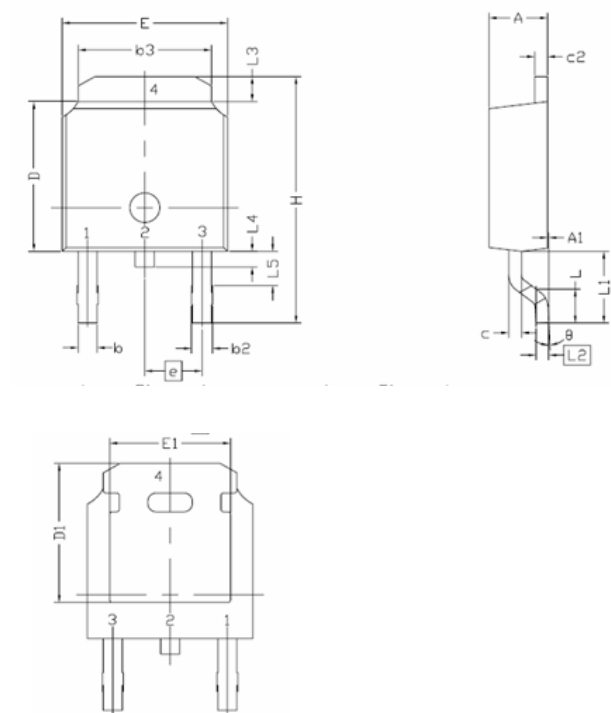


Fig.12 Single Pulse Maximum Power Dissipation

Physical Dimension

D-PAK, 3L

Dimensions are in millimeters, unless otherwise specified



Symbol	Min.	Nom.	Max.
E	6,35	-	6,73
L	1,40	1,52	1,78
L1	2,74 REF		
L2	0,508 BCS		
L3	0,89	-	1,27
L4	-	-	1,02
L5	1,14	-	1,52
D	5,97	6,10	6,22
H	9,40	-	10,41
b	0,64	-	0,89
b2	0,76	-	1,14
b3	4,95	-	5,46
e	2,286 BSC		
A	2,18	-	2,39
A1	-	-	0,13
c	0,46	-	0,61
c2	0,46	-	0,89
D1	5,21	-	-
E1	4,32	-	-
Ø	0,00	-	10,00

Note : Package body size, length and width do not include mold flash, protrusions and gate burrs.

DISCLAIMER:

The Products are not designed for use in hostile environments, including, without limitation, aircraft, nuclear power generation, medical appliances, and devices or systems in which malfunction of any Product can reasonably be expected to result in a personal injury. Seller's customers using or selling Seller's products for use in such applications do so at their own risk and agree to fully defend and indemnify Seller.

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